

What is claimed is:

1. A semiconductor device comprising:
an inner lead having a sloping section sloping upward and outward;
5 a die pad;
a semiconductor chip having an electrode and bonded to the die pad;
a wire electrically connecting the inner lead to the electrode;
a sealing section sealing the inner lead, the semiconductor chip, and the wire;
and
10 an outer lead extending outward from the sealing section.
2. The semiconductor device as defined in claim 1, wherein the wire is bonded to the sloping section.
- 15 3. The semiconductor device as defined in claim 1,
wherein the inner lead further has an end section extending inward from a lower end of the sloping section in a horizontal direction.
4. The semiconductor device as defined in claim 3, wherein the wire is bonded to
20 the end section.
5. The semiconductor device as defined in claim 1,
wherein the inner lead further has a second sloping section sloping downward and outward from a higher end of the sloping section.
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6. The semiconductor device as defined in claim 1,
wherein the inner lead further has a portion extending in a horizontal direction

and connected to the outer lead.

7. The semiconductor device as defined in claim 2,
wherein a bonding position between the wire and the inner lead is lower than
5 the position of the electrode.

8. The semiconductor device as defined in claim 4,
wherein a bonding position between the wire and the inner lead is lower than
the position of the electrode.

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9. The semiconductor device as defined in claim 1,
wherein a surface of the die pad opposite to the semiconductor chip is exposed
from the sealing section.

15 10. A circuit board on which the semiconductor device as defined in claim 1 is
mounted.

11. An electronic instrument comprising the semiconductor device as defined in
claim 1.

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12. A method of manufacturing a semiconductor device, the method comprising:
forming a sloping section sloping upward and outward by bending an inner
lead of a lead frame;

25 bonding a semiconductor chip having an electrode to a die pad of the lead
frame;

electrically connecting the inner lead to the electrode through a wire; and
sealing the inner lead, the semiconductor chip, and the wire.

13. The method of manufacturing a semiconductor device as defined in claim 12,
wherein the wire is bonded to the sloping section.
- 5 14. The method of manufacturing a semiconductor device as defined in claim 12,
further comprising:
forming an end section extending inward from a lower end of the sloping
section in a horizontal direction by bending the inner lead.
- 10 15. The method of manufacturing a semiconductor device as defined in claim 14,
wherein the wire is bonded to the end section.
16. The method of manufacturing a semiconductor device as defined in claim 12,
further comprising:
15 forming a second sloping section sloping downward and outward from a higher
end of the sloping section by bending the inner lead.
17. The method of manufacturing a semiconductor device as defined in claim 12,
further comprising:
20 forming a portion extending in a horizontal direction and outward from a
higher end of the sloping section and bonded to the outer lead of the lead frame.
18. The method of manufacturing a semiconductor device as defined in claim 13,
wherein a bonding position between the wire and the inner lead is made to be
25 lower than the position of the electrode.
19. The method of manufacturing a semiconductor device as defined in claim 15,

wherein a bonding position between the wire and the inner lead is made to be lower than the position of the electrode.

20. The method of manufacturing a semiconductor device as defined in claim 12,
5 further comprising:

exposing a surface of the die pad opposite to the semiconductor chip from the sealing section.